

PENDEOEPIITAXIAL METHODS OF FABRICATING GALLIUM NITRIDE
SEMICONDUCTOR LAYERS ON SAPPHIRE SUBSTRATES,
AND GALLIUM NITRIDE SEMICONDUCTOR STRUCTURES
FABRICATED THEREBY

Abstract Of The Disclosure

More specifically, gallium nitride semiconductor layers may be fabricated by etching an underlying gallium nitride layer on a sapphire substrate, to define at least one post in the underlying gallium nitride layer and at least one trench
5 in the underlying gallium nitride layer. The at least one post includes a gallium nitride top and a gallium nitride sidewall. The at least one trench includes a trench floor. The gallium nitride sidewalls are laterally grown into the at least one trench, to thereby form a gallium nitride semiconductor layer. However, prior to performing the laterally growing step, the sapphire substrate and/or the underlying gallium nitride
10 layer is treated to prevent growth of gallium nitride from the trench floor from interfering with the lateral growth of the gallium nitride sidewalls of the at least one post into the at least one trench. Embodiments of gallium nitride semiconductor structures according to the present invention can include a sapphire substrate and an underlying gallium nitride layer on the sapphire substrate. The underlying gallium
15 nitride layer includes therein at least one post and at least one trench. The at least one post each includes a gallium nitride top and a gallium nitride sidewall. The at least one trench includes a sapphire floor. A lateral gallium nitride layer extends laterally from the gallium nitride sidewall of the at least one post into the at least one trench. In a preferred embodiment, the at least one trench extends into the sapphire substrate
20 such that the at least one post each includes a gallium nitride top, a gallium nitride sidewall and a sapphire sidewall and the at least one trench includes a sapphire floor. The sapphire floor preferably is free of a vertical gallium nitride layer thereon and the sapphire sidewall height to sapphire floor width ratio preferably exceeds about 1/4. A mask may be included on the sapphire floor and an aluminum nitride buffer layer also
25 may be included between the sapphire substrate and the underlying gallium nitride layer. A mask also may be included on the gallium nitride top. ~~The mask on the floor and the mask on the top preferably comprise same material.~~